

# N-Channel 60 V (D-S) Super Junction Power MOSFET

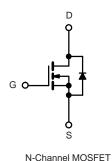
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	I <sub>D</sub> (A) <sup>a</sup>				
60	0.0021 at V <sub>GS</sub> = 10 V	190			
60	0.0029 at V <sub>GS</sub> = 4.5 V	150			

### **FEATURES**

- 175 °C Junction Temperature
- DT-Trench Power MOSFET
- Material categorization:







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ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	$V_{GS}$	± 20	V			
Continuous Drain Current (T <sub>1</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	l <sub>D</sub>	190			
Continuous Diam Current (1 <sub>J</sub> = 175 °C)	T <sub>C</sub> = 100 °C	υD	150 <sup>a</sup>			
Pulsed Drain Current	I <sub>DM</sub>	660	А			
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	190 <sup>a</sup>				
Avalanche Current	I <sub>AS</sub>	189				
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	750	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	235	W		
Maximum Fower Dissipation	T <sub>C</sub> = 75 °C	' D	157	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter			Typical	Maximum	Unit	
Marian and Lunction to Ambient	t ≤ 10 sec	D	10	15		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{thJA}$	30	40	°C/W	
Maximum Junction-to-Case		R <sub>thJC</sub>	0.55	1.0		

#### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10 \text{ s}$ .





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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, } I_D = 250  \mu\text{A}$	60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1		2.5		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		50	μΑ		
		V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	190			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0021	0.0029		
- 1 - 2 - 2 - 1 - b	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.0027	0.0032	0	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C		0.0030	0.0036	Ω	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A		0.0029	0.0039		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS} = 48 \text{ V}, I_{D} = 20 \text{ A}$		45		S	
Dynamic				•			
Input Capacitance	C <sub>iss</sub>			8510			
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 48 V, f = 1 MHz		1070		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			95		]	
Total Gate Charge <sup>c</sup>	Qg			65	77	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		10			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			6.5		1	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			9			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 48 \text{ V}, R_{L} = 0.6 \Omega$		5			
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		52		ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			11			
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				660	Α	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		43	100	ns	

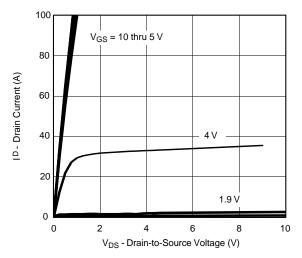
#### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

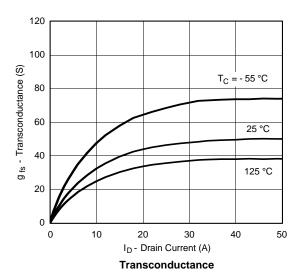
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

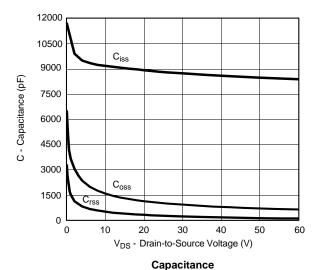


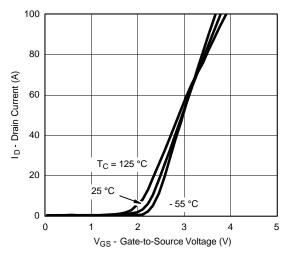
## TYPICAL CHARACTERISTICS (25 °C unless noted)



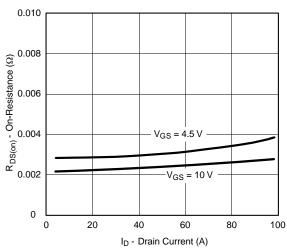
## **Output Characteristics**



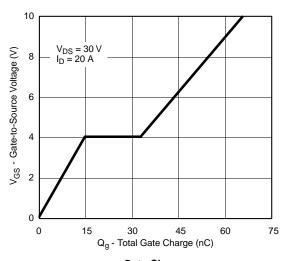




### **Transfer Characteristics**



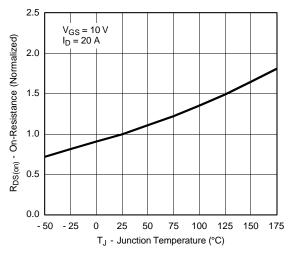
On-Resistance vs. Drain Current



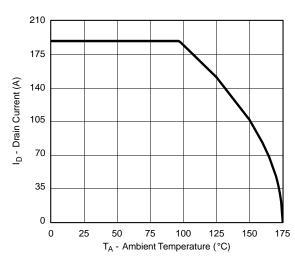
**Gate Charge** 



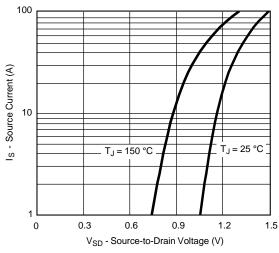
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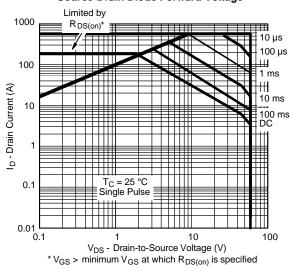
#### On-Resistance vs. Junction Temperature



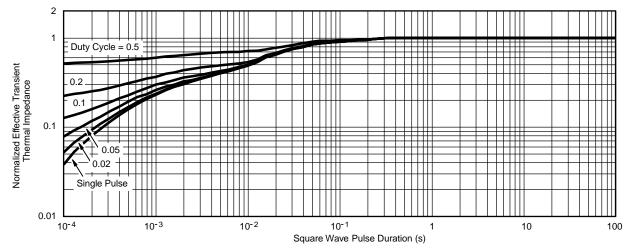
Maximum Drain Current vs. Ambient Temperature



#### Source-Drain Diode Forward Voltage



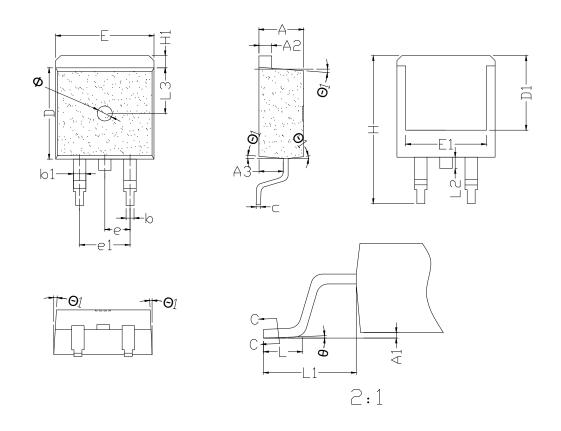
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-263 PACKAGE OUTLINE**



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
Α	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
С	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1		7.50REF		ф	0°	2°	5°
E	9.60	10.02	10.80	φ1	2°	-	7°
E1	7.60	9.88	10.30	Φ		1.5BSC	





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